

## Silicon PNP Power Transistors

## 2N6467 2N6468

## DESCRIPTION

- With TO-66 package
- Excellent safe operating area
- Complement to type 2N6465 2N6466

## APPLICATIONS

- For use in audio amplifier applications

## PINNING(see Fig.2)

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | Base        |
| 2   | Emitter     |
| 3   | Collector   |



Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings( $T_a = \square$ )

| SYMBOL    | PARAMETER                 |        | CONDITIONS        | VALUE   | UNIT      |
|-----------|---------------------------|--------|-------------------|---------|-----------|
| $V_{CBO}$ | Collector-base voltage    | 2N6467 | Open emitter      | -110    | V         |
|           |                           | 2N6468 |                   | -130    |           |
| $V_{CEO}$ | Collector-emitter voltage | 2N6467 | Open base         | -100    | V         |
|           |                           | 2N6468 |                   | -120    |           |
| $V_{EBO}$ | Emitter-base voltage      |        | Open collector    | -5      | V         |
| $I_C$     | Collector current         |        |                   | -4      | A         |
| $P_D$     | Total power dissipation   |        | $T_C = 25\square$ | 40      | W         |
| $T_j$     | Junction temperature      |        |                   | 150     | $\square$ |
| $T_{stg}$ | Storage temperature       |        |                   | -65~150 | $\square$ |

## THERMAL CHARACTERISTICS

| SYMBOL        | PARAMETER                           | VALUE | UNIT        |
|---------------|-------------------------------------|-------|-------------|
| $R_{th\ j-c}$ | Thermal resistance junction to case | 2.5   | $\square/W$ |

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

| SYMBOL                | PARAMETER                            |        | CONDITIONS                                     | MIN  | TYP. | MAX  | UNIT |
|-----------------------|--------------------------------------|--------|------------------------------------------------|------|------|------|------|
| V <sub>CEO(SUS)</sub> | Collector-emitter sustaining voltage | 2N6467 | I <sub>C</sub> =-50mA ; I <sub>B</sub> =0      | -100 |      |      | V    |
|                       |                                      | 2N6468 |                                                | -120 |      |      |      |
| V <sub>CEsat</sub>    | Collector-emitter saturation voltage |        | I <sub>C</sub> =-1.5A ; I <sub>B</sub> =-0.15A |      |      | -1.2 | V    |
| V <sub>BE</sub>       | Base-emitter on voltage              |        | I <sub>C</sub> =-1.5A ; V <sub>CE</sub> =-4V   |      |      | -1.5 | V    |
| I <sub>CBO</sub>      | Collector cut-off current            | 2N6467 | V <sub>CB</sub> =-110V ; I <sub>E</sub> =0     |      |      | -10  | μA   |
|                       |                                      | 2N6468 | V <sub>CB</sub> =-130V ; I <sub>E</sub> =0     |      |      |      |      |
| I <sub>CEO</sub>      | Collector cut-off current            | 2N6467 | V <sub>CE</sub> = -100V, I <sub>B</sub> =0     |      |      | -100 | μA   |
|                       |                                      | 2N6468 | V <sub>CE</sub> = -120V, I <sub>B</sub> =0     |      |      |      |      |
| I <sub>EBO</sub>      | Emitter cut-off current              |        | V <sub>EB</sub> =-5V ; I <sub>C</sub> =0       |      |      | -10  | μA   |
| h <sub>FE</sub>       | DC current gain                      |        | I <sub>C</sub> =-1.5A ; V <sub>CE</sub> =-4V   | 15   |      | 150  |      |
| f <sub>T</sub>        | Transition frequency                 |        | I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-10V  | 5    |      |      | MHz  |

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## PACKAGE OUTLINE

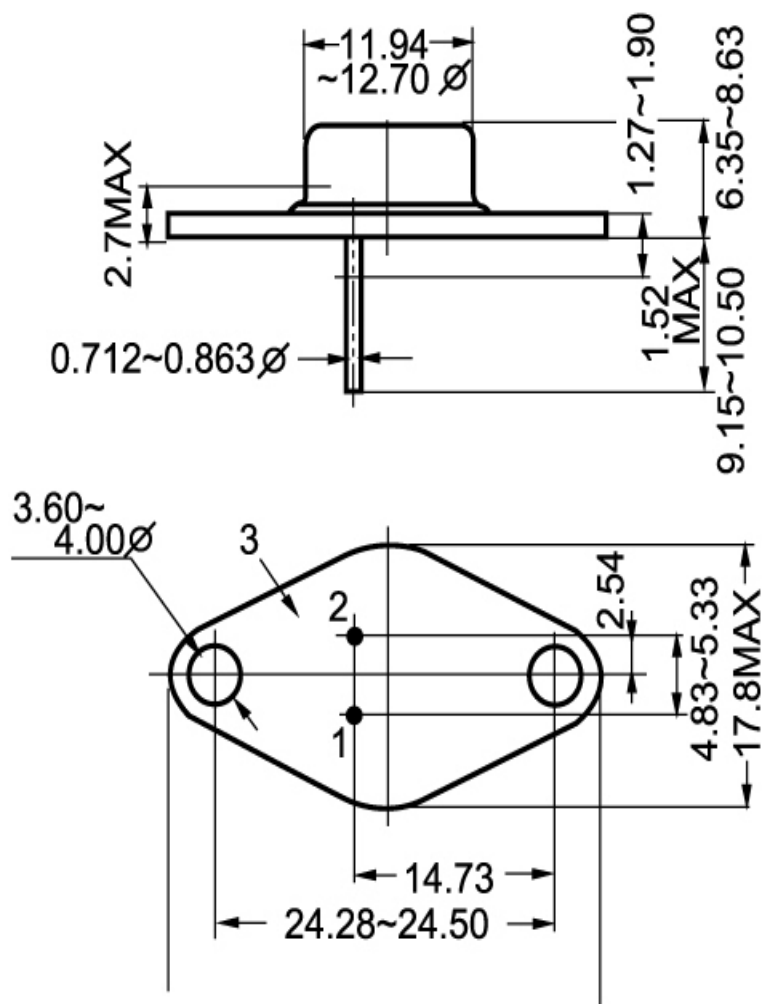


Fig.2 outline dimensions